

Prof. MEHMET KASAP

Personal Information

Office Phone: [+90 312 202 1246](tel:+903122021246)

Email: mkasap@gazi.edu.tr

Web: <https://avesis.gazi.edu.tr/mkasap>

International Researcher IDs

ScholarID: 0VORZowAAAAJ

ORCID: 0000-0001-6214-7620

Publons / Web Of Science ResearcherID: AHE-8287-2022

Yoksis Researcher ID: 2692

Education Information

Doctorate, University of Surrey, England 1990 - 1994

Postgraduate, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Turkey 1985 - 1989

Undergraduate, Firat University, Faculty Of Arts And Sciences, Fizik Mühendisliği Pr., Turkey 1981 - 1985

Dissertations

Doctorate, Temperature and Pressure Dependent of Electron Transport in Plastically Relaxed $In_xGa_{1-x}As$, University of Surrey, 1994

Postgraduate, Enerji band hesaplamalarında APW metodu ve bazı geçiş elementlerine uygulanması, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1988

Research Areas

Surfaces, Interfaces, Thin Films and Nanosystems, Electronic structure of bulk material, Electrical properties of electronic structures, interfaces, thin films and low-dimensional structures, Magnetic Properties and Materials, Optical Properties, Spectroscopy of Matter, Electronic transport in condensed matter

Academic Titles / Tasks

Professor, Gazi University, Fen Fakültesi, Fizik, 2006 - Continues

Associate Professor, Gazi University, Fen Fakültesi, Fizik, 2000 - 2006

Assistant Professor, Gazi University, Fen Fakültesi, Fizik, 1996 - 2000

Research Assistant, Gazi University, Fen Fakültesi, Fizik, 1985 - 1996

Courses

YARIIİLETKEN FİZİĞİ, Undergraduate, 2017 - 2018, 2016 - 2017

TEMEL FİZİK II (ELEKTRİK), Undergraduate, 2017 - 2018

Maddenin Özellikleri, Undergraduate, 2017 - 2018

YARIİLETKEN FİZİĞİ, Postgraduate, 2017 - 2018, 2016 - 2017

TEMEL FİZİK I (MEKANİK), Undergraduate, 2017 - 2018, 2016 - 2017

Advising Theses

KASAP M., The Fabrication Of Au/(Mgo-Pvp) /N-Si (Mps) Schottky Barrier Diodes And The Investigation Their Electrical And Dielectrical Properties, Doctorate, A.EROĞLU(Student), 2021

KASAP M., Investigation Of Structural And Electrical Properties Of Zno Thin Films By Mist Chemical Vapor Deposition Method On Sapphire With Different Orientation, Postgraduate, M.YAYLA(Student), 2021

KASAP M., Forensic Sciences In Terms Of Shot Residue Analysis Techniques And Forensic Applications, Doctorate, İ.KARA(Student), 2014

KASAP M., Electron Transport Properties Of Ingan And Gan Quantum Well Inaln/Gan High Electron Mobility Transistor, Postgraduate, P.NARİN(Student), 2014

KASAP M., The investigation of temperature dependent electrical transport properties of InxGa1-xP/GaAs, Postgraduate, E.BOYALI(Student), 2013

KASAP M., Temperature dependent electrical properties of high doped InxGa1-xAs alloy semiconductor, Postgraduate, E.YAZBAHAR(Student), 2012

KASAP M., Electron and magnetotransport properties of maln/gan based high electron mobility transistors (HEMT), Doctorate, P.TUNAY(Student), 2010

KASAP M., AlGaN/GaN temelli yüksek elektron hareketlilikli transistörlerin (HEMT) elektron ve manyeto iletim özellikleri, Doctorate, S.BORA(Student), 2008

KASAP M., ELECTRON TRANSPORT PROPERTIES OF InxGa1-xN, Doctorate, A.YILDIZ(Student), 2008

KASAP M., AlGaN/GaN TEMELLİ YÜKSEK ELEKTRON HAREKETLİLİKLİ TRANSİSTÖRLERİN (HEMT) ELEKTRON VE MANYETO İLETİM ÖZELLİKLERİ, Doctorate, S.Bora(Student), 2008

KASAP M., LEC tekniği ile büyütülen Zn katkılı InAs yarıiletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Postgraduate, İ.KARA(Student), 2006

KASAP M., MBE tekniği ile büyütülen InGaAs/GaAs ve AlGaAs yarıiletkenlerinin iletim özellikleri, Postgraduate, S.BORA(Student), 2005

KASAP M., LEC tekniği ile büyütülen Te katkılı n-Tipi InSb yarıiletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Postgraduate, Ü.YURDUGÜL(Student), 2005

KASAP M., GaN yarıiletken kristalinde elektron iletimi, Postgraduate, A.YILDIZ(Student), 2004

KASAP M., InAs yarıiletken kristalinde elektron iletimi, Postgraduate, D.DEMİR(Student), 2004

KASAP M., LEC tekniği ile büyütülen bulk InAs yarıiletkenin magneto ve elektron iletim özellikleri, Postgraduate, N.KEREM(Student), 2004

KASAP M., LEC tekniği ile büyütülen Te katkılı n-tipi GaSb yarı iletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Postgraduate, B.YASEMİN(Student), 2004

KASAP M., GaAs ve InP yarıiletkenlerde elektriksel karakterizasyon, Doctorate, S.ACAR(Student), 2003

KASAP M., In0.51Ga0.49As ve In0.60Ga0.40As yarıiletkenlerinde mobilite hesaplamaları, Postgraduate, S.DEMİREZEN(Student), 2001

Published journal articles indexed by SCI, SSCI, and AHCI

I. Temperature dependent electron transport properties of degenerate SnO₂ thin films

Boyalı E., Baran V., ASAR T., Ozcelik S., Kasap M.

JOURNAL OF ALLOYS AND COMPOUNDS, vol.692, pp.119-123, 2017 (SCI-Expanded)

II. Evaluation of morphological and chemical differences of gunshot residues in different ammunitions using SEM/EDS technique

Kara I., Sarikavak Y., LIŞESİVDİN S. B., KASAP M.

ENVIRONMENTAL FORENSICS, vol.17, no.1, pp.68-79, 2016 (SCI-Expanded)

- III. **The Relationship Between the Surface Morphology and Chemical Composition of Gunshot Residue Particles**
Kara I., LİŞESİVDİN S. B., Kasap M., Er E., Uzek U.
JOURNAL OF FORENSIC SCIENCES, vol.60, no.4, pp.1030-1033, 2015 (SCI-Expanded)
- IV. **Electron Transport Properties of Two-Dimensional Electron Gas in $\text{Be}_x\text{Zn}_{1-x}\text{O}/\text{ZnO}$ Heterostructures**
Atmaca G., Narin P., Lisesivdin S. B., Kasap M., Sarikavak-Lisesivdin B.
PHILOSOPHICAL MAGAZINE, vol.95, no.1, pp.79-89, 2015 (SCI-Expanded)
- V. **Analysis Of The Number Of Shots Using Graphite Furnace Atomic Absorption Spectrometry On The Gunshot Residues Deposited in The Barrel**
KARA İ., YALÇINKAYA Ö., LİŞESİVDİN S. B., KASAP M.
SYLWAN, vol.159, no.1, pp.14-26, 2015 (SCI-Expanded)
- VI. **Study on growth and characterizations of $\text{Ga}_{1-x}\text{In}_x\text{P}/\text{GaAs}$ solar cell structure**
Kinacı B., Özen Y., Asar T., Cetin S. Ş., Memmedli T., Kasap M., Ozcelik S.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.24, no.9, pp.3269-3274, 2013 (SCI-Expanded)
- VII. **Investigation of AlInN HEMT structures with different AlGaIn buffer layers grown on sapphire substrates by MOCVD**
Kelekci O., Tasli P., Cetin S. Ş., Kasap M., Ozcelik S., Ozbay E.
CURRENT APPLIED PHYSICS, vol.12, no.6, pp.1600-1605, 2012 (SCI-Expanded)
- VIII. **Electron transport properties in $\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}/\text{AlN}/\text{GaN}$ heterostructures with different InGaIn back barrier layers and GaN channel thicknesses grown by MOCVD**
Kelekci O., Tasli P. T., Yu H., KASAP M., ÖZÇELİK S., ÖZBAY E.
PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, vol.209, no.3, pp.434-438, 2012 (SCI-Expanded)
- IX. **Epitaxial growth and electrical characterization of germanium**
Bosi M., Attolini G., Ferrari C., Frigeri C., Calicchio M., Gombia E., Asar T., Boyali E., Aydemir U., Ozcelik S., et al.
CRYSTAL RESEARCH AND TECHNOLOGY, vol.46, no.8, pp.813-817, 2011 (SCI-Expanded)
- X. **Grain Boundary Related Electrical Transport in Al-rich $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Layers Grown by Metal-Organic Chemical Vapor Deposition**
Yildiz A., Tasli P., Sarikavak B., Lisesivdin S. B., Ozturk M. K., Kasap M., Ozcelik S., Ozbay E.
SEMICONDUCTORS, vol.45, no.1, pp.33-36, 2011 (SCI-Expanded)
- XI. **Electron-Electron Interactions in Sb-Doped SnO_2 Thin Films**
Serin T., Yildiz A., SERİN N., Yildirim N., Ozyurt F., KASAP M.
JOURNAL OF ELECTRONIC MATERIALS, vol.39, no.8, pp.1152-1158, 2010 (SCI-Expanded)
- XII. **The substrate temperature dependent electrical properties of titanium dioxide thin films**
Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.21, no.7, pp.692-697, 2010 (SCI-Expanded)
- XIII. **Double subband occupation of the two-dimensional electron gas in $\text{In}_x\text{Al}_{1-x}\text{N}/\text{AlN}/\text{GaN}/\text{AlN}$ heterostructures with a low indium content ($0.064 \leq x \leq 0.140$) barrier**
LİŞESİVDİN S. B., Tasli P., Kasap M., Ozturk M., Arslan E., Ozcelik S., Ozbay E.
THIN SOLID FILMS, vol.518, no.19, pp.5572-5575, 2010 (SCI-Expanded)
- XIV. **Scattering analysis of two-dimensional electrons in $\text{AlGaIn}/\text{GaIn}$ with bulk related parameters extracted by simple parallel conduction extraction method**
Lisesivdin S. B., Yildiz A., Balkan N., Kasap M., Ozcelik S., Ozbay E.
JOURNAL OF APPLIED PHYSICS, vol.108, no.1, 2010 (SCI-Expanded)
- XV. **Determination of the critical indium composition corresponding to the metal-insulator transition in $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0.06 \leq x \leq 0.135$) layers**
Yildiz A., LİŞESİVDİN S. B., Tasli P., Ozbay E., Kasap M.
CURRENT APPLIED PHYSICS, vol.10, no.3, pp.838-841, 2010 (SCI-Expanded)
- XVI. **The temperature dependence of the inelastic scattering time in InGaIn grown by MOVPE**
Yildiz A., Kasap M.

- LOW TEMPERATURE PHYSICS, vol.36, no.4, pp.320-324, 2010 (SCI-Expanded)
- XVII. **Analysis of defect related optical transitions in biased AlGa_N/Ga_N heterostructures**
Bengi A., LİŞESİVDİN S. B., Kasap M., Mammadov T., Ozcelik S., Ozbay E.
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, vol.13, no.2, pp.105-108, 2010 (SCI-Expanded)
- XVIII. **The thickness effect on the electrical conduction mechanism in titanium oxide thin films**
Yildiz A., Serin N., Kasap M., Serin T., Mardare D.
JOURNAL OF ALLOYS AND COMPOUNDS, vol.493, pp.227-232, 2010 (SCI-Expanded)
- XIX. **Investigation of low-temperature electrical conduction mechanisms in highly resistive Ga_N bulk layers extracted with Simple Parallel Conduction Extraction Method**
Yildiz A., LİŞESİVDİN S. B., Kasap M., Ozcelik S., Ozbay E., Balkan N.
APPLIED PHYSICS A-MATERIALS SCIENCE & PROCESSING, vol.98, no.3, pp.557-563, 2010 (SCI-Expanded)
- XX. **Well parameters of two-dimensional electron gas in Al_{0.88}In_{0.12}N/Al_N/Ga_N/Al_N heterostructures grown by MOCVD**
Tasli P., LİŞESİVDİN S. B., Yildiz A., Kasap M., Arslan E., Ozcelik S., Ozbay E.
CRYSTAL RESEARCH AND TECHNOLOGY, vol.45, no.2, pp.133-139, 2010 (SCI-Expanded)
- XXI. **Contributions of impurity band and electron-electron interactions to magnetoconductance in AlGa_N**
Tasli P., Yildiz A., Kasap M., Ozbay E., LİŞESİVDİN S. B., Ozcelik S.
PHILOSOPHICAL MAGAZINE, vol.90, no.26, pp.3591-3599, 2010 (SCI-Expanded)
- XXII. **Electrical conduction properties of Si delta-doped GaAs grown by MBE**
Yildiz A., LİŞESİVDİN S. B., Altuntas H., Kasap M., Ozcelik S.
PHYSICA B-CONDENSED MATTER, vol.404, no.21, pp.4202-4206, 2009 (SCI-Expanded)
- XXIII. **Crossover from Nearest-Neighbor Hopping Conduction to Efros-Shklovskii Variable-Range Hopping Conduction in Hydrogenated Amorphous Silicon Films**
Yildiz A., SERİN N., Serin T., KASAP M.
JAPANESE JOURNAL OF APPLIED PHYSICS, vol.48, no.11, 2009 (SCI-Expanded)
- XXIV. **The effect of intrinsic defects on the hole transport in Cu₂O**
Yildiz A., Serin N., Serin T., Kasap M.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.3, no.10, pp.1034-1037, 2009 (SCI-Expanded)
- XXV. **Structural, electrical and optical characterization of InGa_N layers grown by MOVPE**
Yildiz A., Kemal O. M., Bosi M., Ozcelik S., Kasap M.
CHINESE PHYSICS B, vol.18, no.9, pp.4007-4012, 2009 (SCI-Expanded)
- XXVI. **DX-center energy calculation with quantitative mobility spectrum analysis in n-AlGaAs/GaAs structures with low Al content**
LİŞESİVDİN S. B., Altuntas H., Yildiz A., Kasap M., Ozbay E., Ozcelik S.
SUPERLATTICES AND MICROSTRUCTURES, vol.45, no.6, pp.604-611, 2009 (SCI-Expanded)
- XXVII. **Numerical optimization of Al-mole fractions and layer thicknesses in normally-on AlGa_N-Ga_N double-channel high electron mobility transistors (DCHEMTs)**
Atmaca G., Elibol K., LİŞESİVDİN S. B., Kasap M., Ozbay E.
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, vol.11, no.5, pp.578-582, 2009 (SCI-Expanded)
- XXVIII. **Large zero-field spin splitting in AlGa_N/Al_N/Ga_N/Al_N heterostructures**
LİŞESİVDİN S. B., Balkan N., Makarovskiy O., Patane A., Yildiz A., Caliskan M. D., Kasap M., Ozcelik S., Ozbay E.
JOURNAL OF APPLIED PHYSICS, vol.105, no.9, 2009 (SCI-Expanded)
- XXIX. **Non-adiabatic small polaron hopping conduction in Nb-doped TiO₂ thin film**
Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.
PHYSICA B-CONDENSED MATTER, vol.404, pp.1423-1426, 2009 (SCI-Expanded)
- XXX. **Anomalous temperature dependence of the electrical resistivity in In_{0.17}Ga_{0.83}N**
Yildiz A., LİŞESİVDİN S. B., Kasap M., Bosi M.
SOLID STATE COMMUNICATIONS, vol.149, pp.337-340, 2009 (SCI-Expanded)
- XXXI. **Comparison of the transport properties of high quality AlGa_N/Al_N/Ga_N and AlIn_N/Al_N/Ga_N two-dimensional electron gas heterostructures**

- TÜLEK R., ILGAZ A., GÖKDEN S., TEKE A., Ozturk M. K., KASAP M., Ozcelik S., Arslan E., ÖZBAY E.
JOURNAL OF APPLIED PHYSICS, vol.105, no.1, 2009 (SCI-Expanded)
- XXXII. **Electrical properties of TiO(2) thin films**
Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.
JOURNAL OF NON-CRYSTALLINE SOLIDS, vol.354, pp.4944-4947, 2008 (SCI-Expanded)
- XXXIII. **Growth parameter investigation of Al_{0.25}Ga_{0.75}N/GaN/AlN heterostructures with Hall effect measurements**
LİŞESİVDİN S. B., Demirezen S., Caliskan M. D., Yildiz A., Kasap M., Ozcelik S., Ozbay E.
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, vol.23, no.9, 2008 (SCI-Expanded)
- XXXIV. **The persistent photoconductivity effect in AlGa_xN/GaN heterostructures grown on sapphire and SiC substrates**
Arslan E., Butun S., LİŞESİVDİN S. B., KASAP M., ÖZÇELİK S., ÖZBAY E.
JOURNAL OF APPLIED PHYSICS, vol.103, no.10, 2008 (SCI-Expanded)
- XXXV. **Stokes shift and band gap bowing in In_xGa_{1-x}N (0.060 ≤ x ≤ 0.105) grown by metalorganic vapour phase epitaxy**
Yildiz A., Dagdelen F., ACAR S., LİŞESİVDİN S. B., Kasap M., AYDOĞDU Y., Bosi M.
ACTA PHYSICA POLONICA A, vol.113, no.2, pp.731-739, 2008 (SCI-Expanded)
- XXXVI. **Determination of two-dimensional electron and hole gas carriers in AlGa_xN/GaN/AlN heterostructures grown by Metal Organic Chemical Vapor Deposition**
ACAR S., LİŞESİVDİN S. B., Kasap M., Oezcelik S., Oezbay E.
THIN SOLID FILMS, vol.516, no.8, pp.2041-2044, 2008 (SCI-Expanded)
- XXXVII. **Self-consistent scattering analysis of Al_{0.2}Ga_{0.8}N/AlN/GaN/AlN heterostructures grown on 6H-SiC substrates using photo-Hall effect measurements**
LİŞESİVDİN S. B., Arslan E., Kasap M., Ozcelik S., Ozbay E.
JOURNAL OF PHYSICS-CONDENSED MATTER, vol.20, no.4, 2008 (SCI-Expanded)
- XXXVIII. **The effect of strain relaxation on electron transport in undoped Al_{0.25}Ga_{0.75}N/GaN heterostructures**
LİŞESİVDİN S. B., Yildiz A., ACAR S., Kasap M., Oezcelik S., Oezbay E.
PHYSICA B-CONDENSED MATTER, vol.399, no.2, pp.132-137, 2007 (SCI-Expanded)
- XXXIX. **Electron transport in Ga-rich In_xGa_{1-x}N alloys**
Yildiz A., LİŞESİVDİN S. B., ACAR S., Kasap M., Bosi M.
CHINESE PHYSICS LETTERS, vol.24, no.10, pp.2930-2933, 2007 (SCI-Expanded)
- XL. **Electronic transport characterization of AlGa_xN/GaN heterostructures using quantitative mobility spectrum analysis**
LİŞESİVDİN S. B., Yildiz A., ACAR S., Kasap M., Ozcelik S., Ozbay E.
APPLIED PHYSICS LETTERS, vol.91, no.10, 2007 (SCI-Expanded)
- XLI. **Temperature-dependent electron transport in In_{0.5}Ga_{0.5}P/GaAs grown by MOVPE**
ACAR S., Yildiz A., Kasap M., Bosi M.
CHINESE PHYSICS LETTERS, vol.24, no.8, pp.2373-2375, 2007 (SCI-Expanded)
- XLII. **Scattering analysis of 2DEG carrier extracted by QMSA in undoped Al_{0.25}Ga_{0.75}N/GaN heterostructures**
LİŞESİVDİN S. B., ACAR S., Kasap M., Ozcelik S., Gokden S., Ozbay E.
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, vol.22, no.5, pp.543-548, 2007 (SCI-Expanded)
- XLIII. **High temperature variable-range hopping conductivity in undoped TiO₂ thin film**
Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.1, no.10, pp.531-533, 2007 (SCI-Expanded)
- XLIV. **Optimization of alloy composition, interlayer and barrier thicknesses in Al_xGa_{1-x}N/(AlN)/GaN high electron mobility transistors**
LİŞESİVDİN S. B., Yildiz A., Kasap M.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.1, no.9, pp.467-470, 2007 (SCI-

Expanded)

- XLV. **Quantitative mobility spectrum analysis for determination of electron and magneto transport properties of Te-doped GaSb**
ACAR S., Kasap M., Isik B., Ozcelik S., Tugluoglu N., Karadeniz S.
Chinese Physics Letters, vol.22, no.9, pp.2363-2366, 2005 (SCI-Expanded)
- XLVI. **Temperature-dependent galvanomagnetic measurements on doped InSb and InAs grown by liquid encapsulated czochralski**
Kasap M., ACAR S., Ozcelik S., Karadeniz S., Tugluoglu N.
Chinese Physics Letters, vol.22, no.5, pp.1218-1221, 2005 (SCI-Expanded)
- XLVII. **The temperature dependence of electron and magneto transport properties in Te-doped InSb**
Kasap M., ACAR S.
PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, vol.201, no.14, pp.3113-3120, 2004 (SCI-Expanded)
- XLVIII. **Temperature-dependent barrier characteristics of inhomogeneous in/p-Si (100) Schottky barrier diodes**
Tugluoglu N., Karadeniz S., ACAR S., Kasap M.
CHINESE PHYSICS LETTERS, vol.21, no.9, pp.1795-1798, 2004 (SCI-Expanded)
- XLIX. **Gaussian distribution of inhomogeneous barrier height in Ag/p-Si (100) Schottky barrier diodes**
ACAR S., Karadeniz S., Tugluoglu N., Selcuk A., Kasap M.
APPLIED SURFACE SCIENCE, vol.233, pp.373-381, 2004 (SCI-Expanded)
- L. **Conductivity, Hall and magnetoresistance effect measurements on SiGaAs and InP**
ACAR S., Kasap M.
PHYSICA STATUS SOLIDI A-APPLIED RESEARCH, vol.201, no.7, pp.1551-1557, 2004 (SCI-Expanded)
- LI. **Prebreakdown current behaviour in the ionization cell with a semiconductor cathode**
Salamov B., Kasap M., Lebedeva N.
JOURNAL OF PHYSICS D-APPLIED PHYSICS, vol.33, no.17, pp.2192-2195, 2000 (SCI-Expanded)
- LII. **The simulation of the two-dimensional Ising model in the presence of an external magnetic field on the Creutz cellular automaton**
Kutlu B., Kasap M., Turan S.
INTERNATIONAL JOURNAL OF MODERN PHYSICS C, vol.11, no.3, pp.561-572, 2000 (SCI-Expanded)
- LIII. **The concentration of currents on the artificial surface inhomogeneities of semiconducting cathodes in ionization cells**
Salamov B., Ozer M., Kasap M., Altindal Ş.
JOURNAL OF PHYSICS D-APPLIED PHYSICS, vol.32, no.6, pp.682-687, 1999 (SCI-Expanded)
- LIV. **The temperature and pressure dependence of electron transport in plastically relaxed In_xGa_{1-x}As**
Kasap M., Lancefield D.
PHYSICA STATUS SOLIDI B-BASIC RESEARCH, vol.199, no.2, pp.481-493, 1997 (SCI-Expanded)
- LV. **The rapid visualization of resistivity inhomogeneities in high-resistivity semiconductor films**
Salamov B., Civi M., Altindal Ş., Kasap M., BULUR E.
JOURNAL OF INFORMATION RECORDING, vol.23, no.5, pp.437-445, 1997 (SCI-Expanded)
- LVI. **Impurity conduction in In_xGa_{1-x}As**
KASAP M., ÖZER M., Çolakoğlu K.
Turkish Journal of Physics, vol.20, no.7, pp.740-746, 1996 (SCI-Expanded)

Refereed Congress / Symposium Publications in Proceedings

- I. **Determination of Structural and Electrical Properties of ZnO Thin Films Grown By Mist-Cvd Method on Sapphire with Different Orientations**
Yayla M., LIŞESİVDİN S. B., KASAP M.
Turkish Physical Society 37th International Physics Congress, Muğla, Turkey, 01 September 2021, pp.236

- II. **The Study on Antimony Diffusion in Gallium-Doped Germanium Grown by Chochralski Technique**
Baran V., Çat Y., Akin Sönmez N., Özen Y., Kasap M., Özçelik S.
Turkish Physical Society 33th International Physics Congress, Muğla, Turkey, 6 - 10 September 2017
- III. **The Study on Antimony Diffusion in Gallium-doped Germanium Grown by Czochralski Technique**
Baran V., Çat Y., Akin Sönmez N., Özen Y., Kasap M., Özçelik S.
Turkish Physical Society 33th International Physics Congress (TFD33), Muğla, Turkey, 6 - 10 September 2017
- IV. **Pt Metal Kümelerin Katkısız SnO₂ Sensör Yapılarının Algılama Özelliklerine Etkisi**
Boyalı E., Korkmaz B., Sertel T., Efkere H. İ., Özen Y., Çetin S. Ş., Özçelik S., Kasap M.
22. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Turkey, 16 December 2016
- V. **Germanyum Kızıl Ötesi Optik Pencereleler ve Elektromanyetik Girişim**
Çat Y., Baran V., Kasap M., Özçelik S.
22. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Turkey, 16 December 2016
- VI. **Sb Doping Effect on the Electrical Properties of Germanium Single Crystals**
BARAN V., ÇAT Y., BOYALI E., ASAR T., KASAP M., ÖZÇELİK S.
2nd International Congress on The World of Technology and Advanced Materials (WITAM2016), Kırşehir, Turkey, 28 September - 02 October 2016
- VII. **Sb Katkılı Hacimli Germanyum Tek Kristal Büyütülmesi ve Karakterizasyonu**
Baran V., Çat Y., Asar T., Çetin S. Ş., Kasap M., Özçelik S.
21. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Turkey, 25 December 2015
- VIII. **Electrical, Optical And Structural Properties of SnO₂ Thin Films**
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Metrics

Publication: 109
Citation (WoS): 1009
Citation (Scopus): 969
H-Index (WoS): 17
H-Index (Scopus): 17

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